

# Nano-Imprint Lithography (NIL)

By *Lihui Wang*

# Outline

---

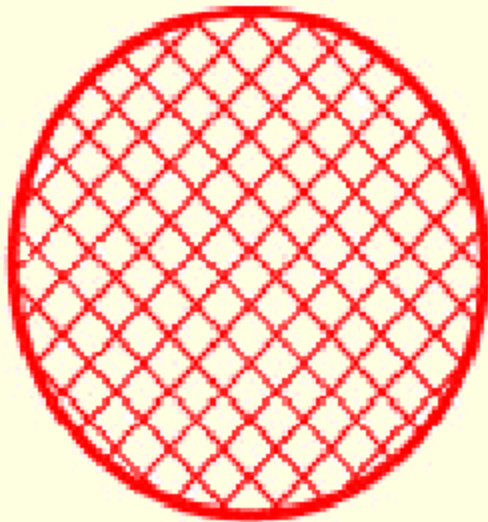
- Introduction
- Process
- Applications
- Advantages and Challenges
- Conclusions
- References

# Introduction

---

Lithography: Producing desired pattern on a substrate

Nanolithography: lithography with feature-size less than 100nm



Conventional  
photolithography~ 500nm

Deep UV  
photolithography~ 120nm

E-Beam/X-ray  
lithography~ <50nm

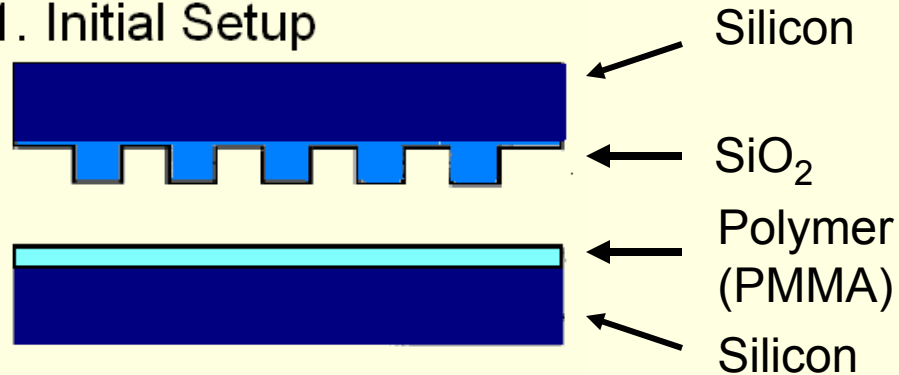
# Introduction

---

- Photolithography is economically impractical for mass production of sub-50nm structures
- Imprint technology using compression molding of thermoplastic polymers is known as a low-cost mass manufacturing technology
- Is it possible to apply the imprint technology to lithography?

# Process: Schematic View

## 1. Initial Setup



## 2. imprinting



## 3. Mold release



Mold Contact



Pressing



Mold Release



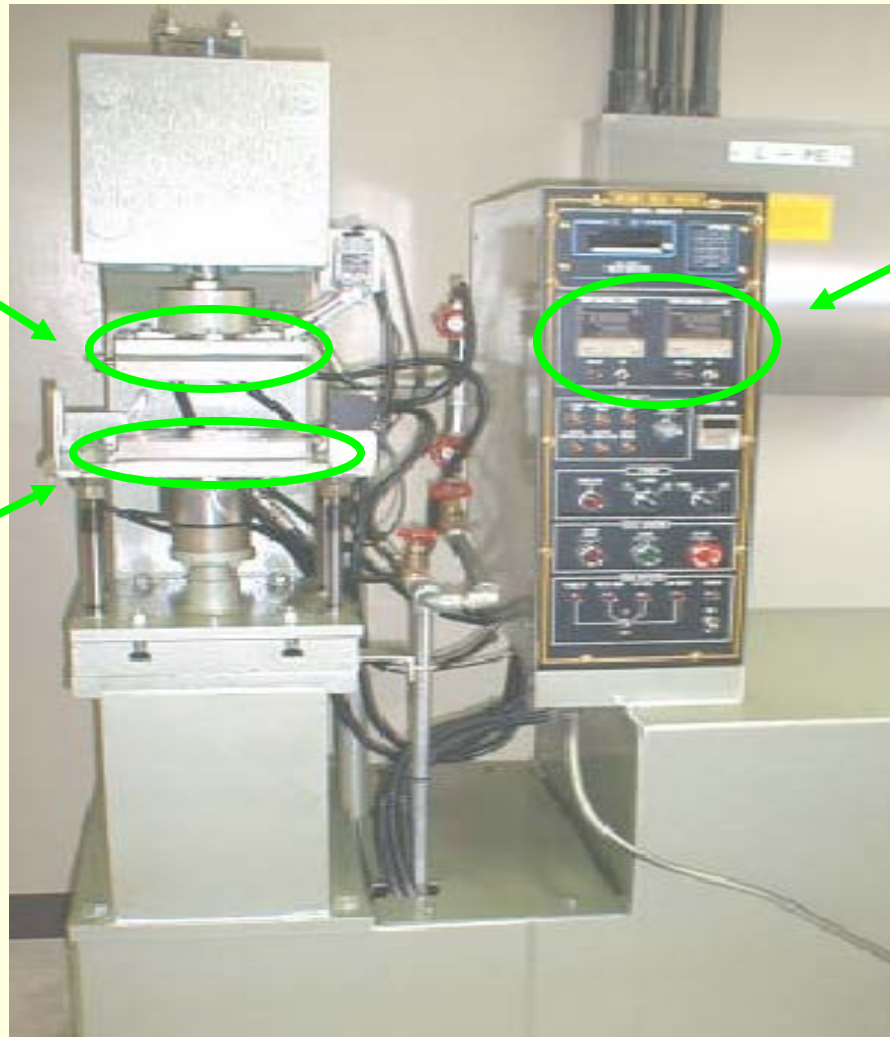
Residual polymer  
removal using RIE

# Process: Practical View

---

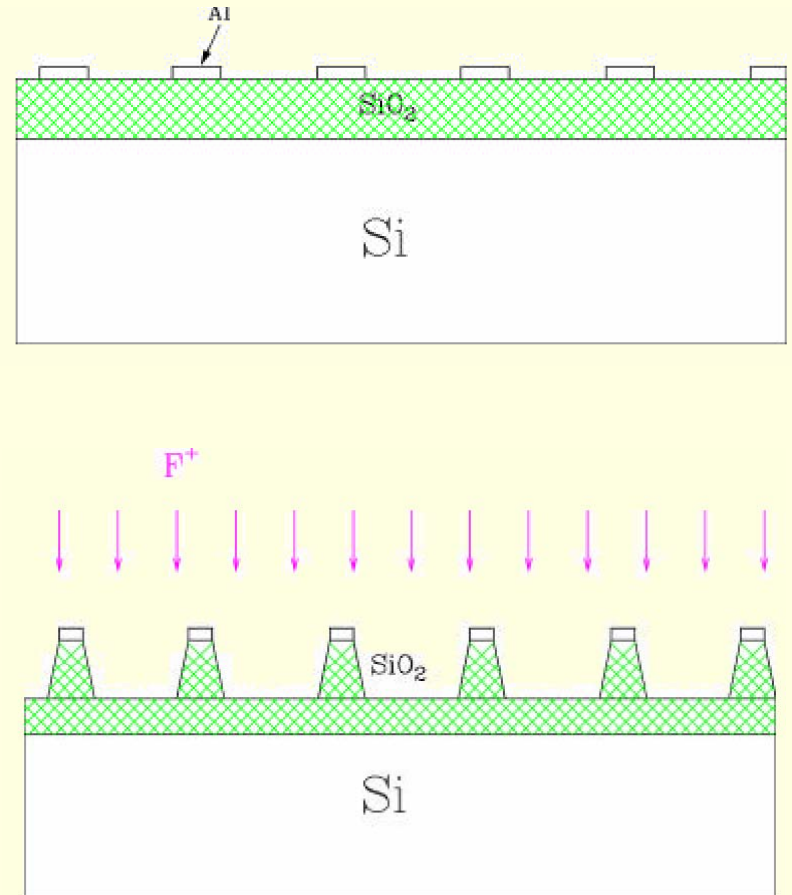
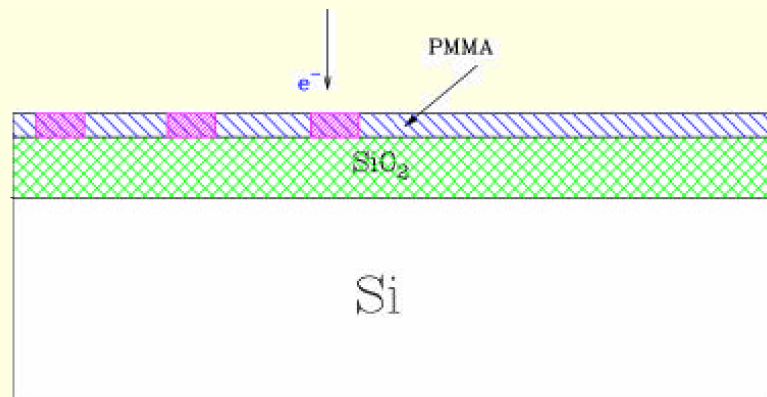
Upper  
Plate

Lower  
Plate



Heat  
Control  
Panel

# Process: Mask Fabrication



# Process: Polymer Consideration

---

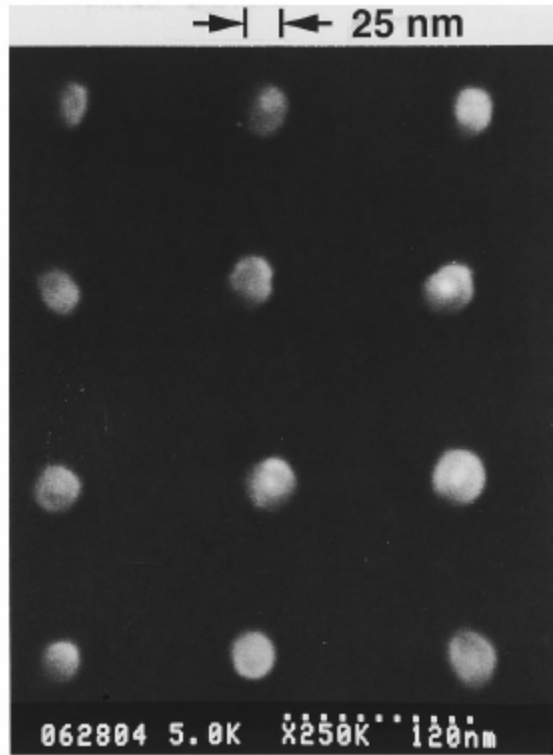
- Mold release property: not adhere to mold
- Shrinkage: small shrinkage due to temperature and pressure variance.

PMMA (Polymethylmethacrylate) :

- hydrophilic surface( not adhere to  $\text{SiO}_2$ )
- Less than 0.5% shrinkage at processing conditions.
- Glass-transition temperature  $T_g=105^\circ\text{C}$



# Process: Created Patterns

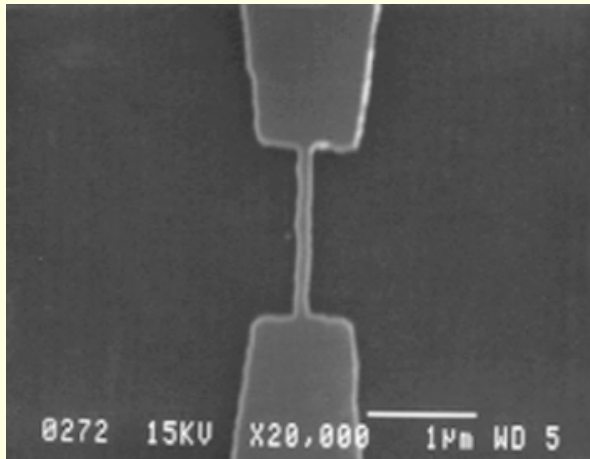


SEM micrograph of Ti/Au dot pattern on a silicon substrate fabricated by NIL [1]

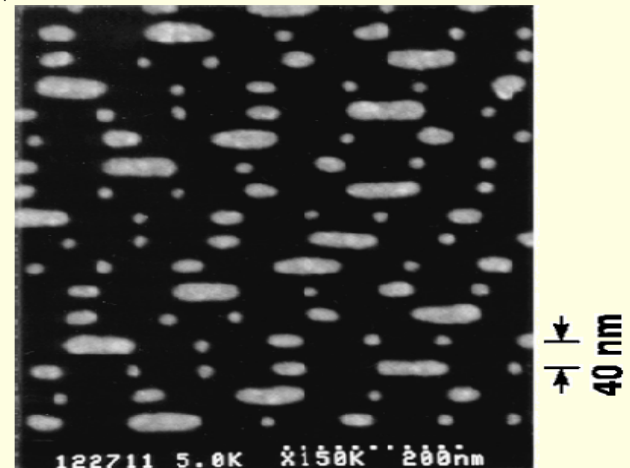
- RIE is used to cut down resist thickness until shallow regions are completely removed
- Ti/Au is deposited on resist
- Resist and metal coating is removed (by liftoff process) leaving metal dots with 25nm diameter and 120 nm period

# Applications

- Quantum dot, Quantum wire
- Nanocompact disk



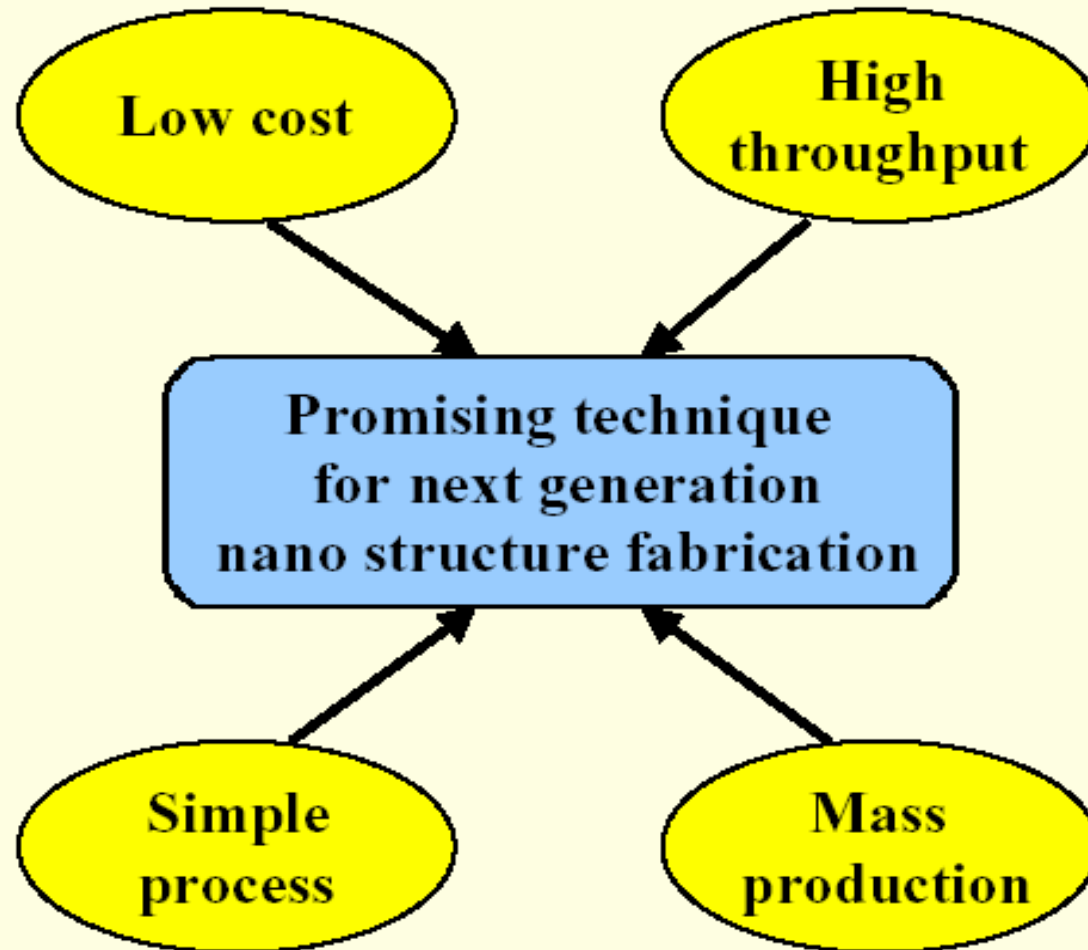
100nm wire channel MOSFET[2]



Nano-CD of 40nm track width [2]

# Advantages

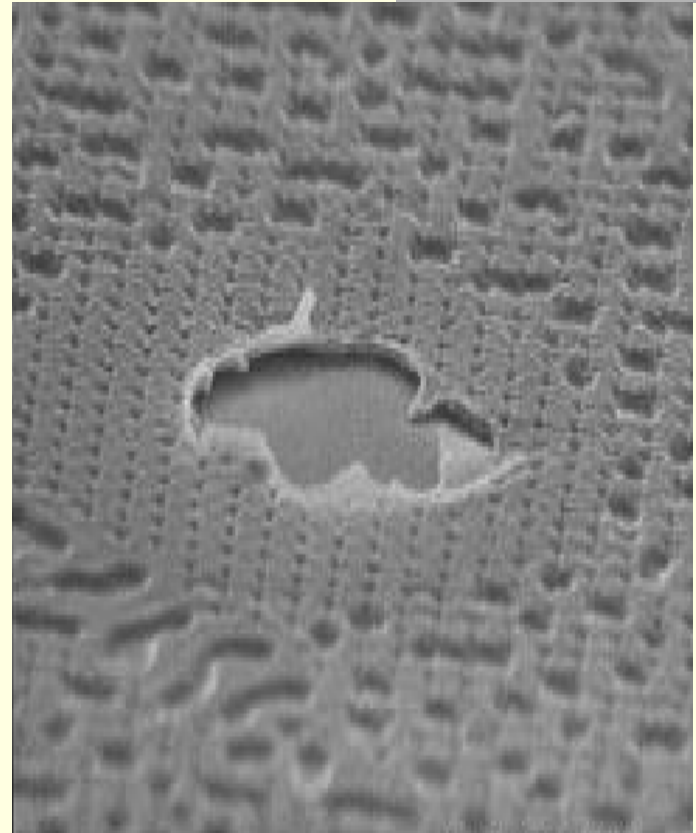
---



# Limitations and Problems

---

- Global fidelity of patterns
- Multilevel alignment
- Large imprint areas
- Tearing of polymer



# Conclusions

---

- NIL is a high throughput low-cost method to develop sub-100nm structures.
- Sticking and defect problems associated with the traditional contact printing exist.
- With a proper selection of the polymer and mold materials and an optimization of the pressing conditions, these problems may be solved.

# References

---

- [1] Stephen Chou & et al :Imprint of sub-25nm  
vias and trenches in polymers
- [2] Stephen Chou & et al :Sub-10nm imprint  
lithography and applications